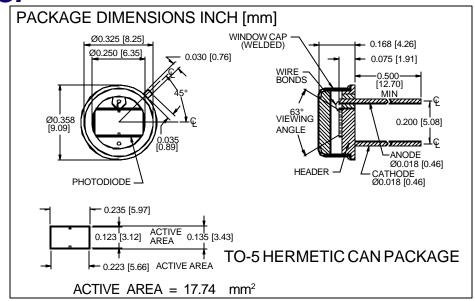
PHOTONIC Silicon Photodiode, U.V. Enhanced Photoconductive **DETECTORS INC.** Type PDU-C114





FEATURES

- High speed
- U.V. enhanced
- Low capacitance
- U.V. window

DESCRIPTION

The **PDU-C114** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-5 metal can with a U.V. transmitting window.

APPLICATIONS

- Spectrometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

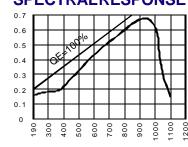
RESPONSIVITY (A/W)

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER MIN		MAX	UNITS	
VBR	Reverse Voltage		30	V	
T _{STG}	Storage Temperature	-55	+150	⊙C	
То	Operating Temperature Range	-40	+125	∘C	
Ts	Soldering Temperature*		+240	∘C	
IL	Light Current		500	mA	

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	190	235		μΑ
ΙD	Dark Current	$H = 0, V_R = 5 V$		3	8	nA
RsH	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	75	250		ΜΩ
TC Rsh	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
CJ	Junction Capacitance	$H = 0, V_R = 5 V^{**}$		200		рF
λrange	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	$V_{R} = 0 \text{ V}, \lambda = 254 \text{ nm}$.12	.18		A/W
V _{BR}	Breakdown Voltage	Ι = 10 μΑ	15	25		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		3.8x10 ⁻¹⁴		W/√Hz
tr	Response Time	$RL = 1 K\Omega V_R = 5 V$		65		nS